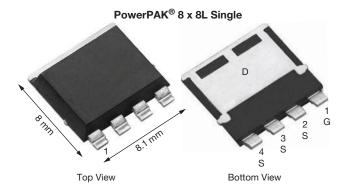
SQJQ480E



Vishay Siliconix

Automotive N-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	80					
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.003					
I _D (A)	150					
Configuration	Single					
Package	PowerPAK 8 x 8L					



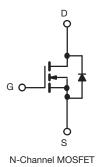
FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



HALOGEN

FREE



ABSOLUTE MAXIMUM RATINGS (TC	; = 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	80	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C	I_	150	
Continuous Drain Current	T _C = 125 °C	Ι _D	87	
Continuous Source Current (Diode conduction)	I _S	124	А	
Pulsed Drain Current ^a		I _{DM}	210	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	53	
Single Pulse Avalanche Energy		E _{AS}	140	mJ
Maximum Power Dissipation	T _C = 25 °C	PD	136	W
	T _C = 125 °C	гD	45	vv
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak temperature) c.	, d		260	U

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB mount ^b	R _{thJA}	50	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.1	0/10

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR4 material).

c. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SQJQ480E

SPECIFICATIONS ($T_C = 25 \circ C$, unless othe	erwise noted)					
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•	•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	80	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	2.5	3	3.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V_{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 80 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 80 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	500	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	А
		$V_{GS} = 10 V$	I _D = 20 A	-	0.0024	0.0030	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	$I_D = 20 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.0048	Ω
		$V_{GS} = 10 V$	I _D = 20 A, T _J = 175 °C	-	-	0.0060	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 15 A	-	82	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	6900	8625	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	3655	4570	pF
Reverse Transfer Capacitance	C _{rss}			-	250	311	
Total Gate Charge ^c	Qg			-	82	144	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 40 \text{ V}, I_D = 10 \text{ A}$	-	11	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	21	-	
Gate Resistance	R _g	f = 1 MHz		0.4	0.8	1.2	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	19	30	
Rise Time ^c	t _r	V _{DD}	= 40 V, R_{L} = 4 Ω	-	7.3	11	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A},$	V_{GEN} = 10 V, R_g = 1 Ω	-	40	60	ns
Fall Time ^c	t _f]		-	15	23	
Source-Drain Diode Ratings and Cha	racteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	210	А
Forward Voltage	V _{SD}	I _F =	40 A, V _{GS} = 0 V	-	0.7	1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

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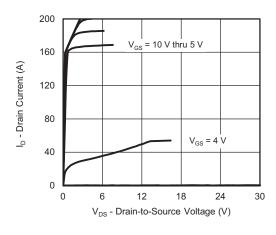
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

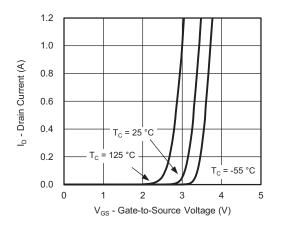
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



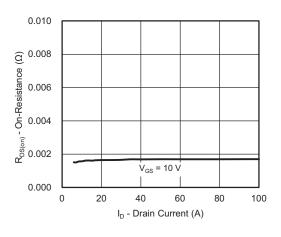
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



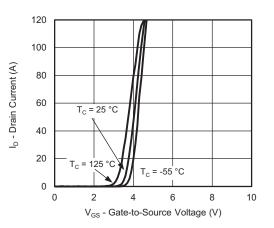
Output Characteristics



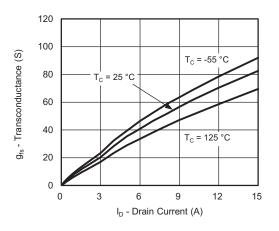
Transfer Characteristics



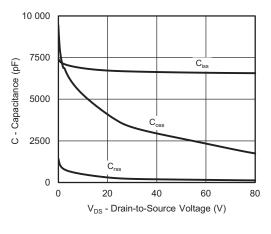
On-Resistance vs. Drain Current



Transfer Characteristics



Transconductance



Capacitance

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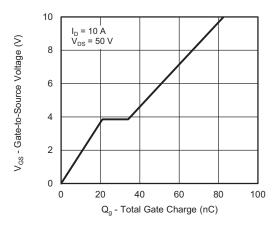
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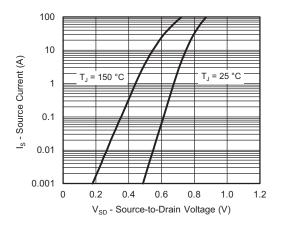
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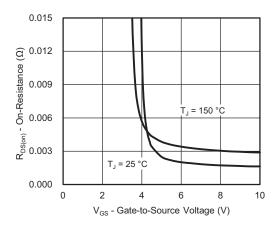
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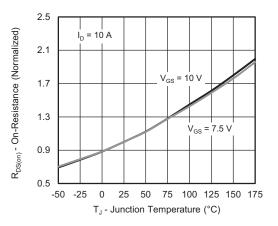
Gate Charge



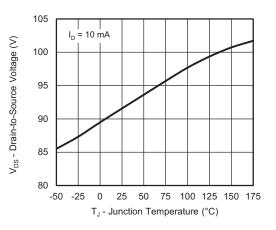
Source Drain Diode Forward Voltage



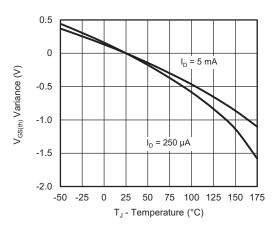
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature



Threshold Voltage

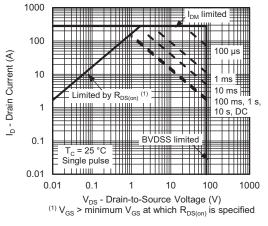
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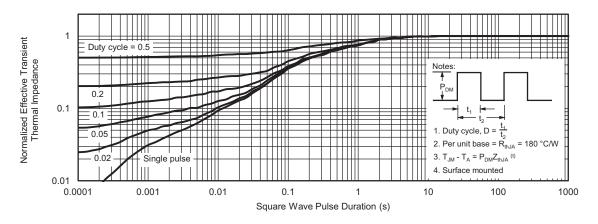


TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

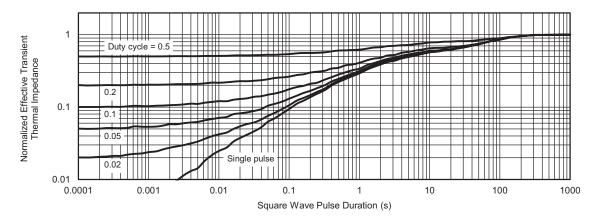
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

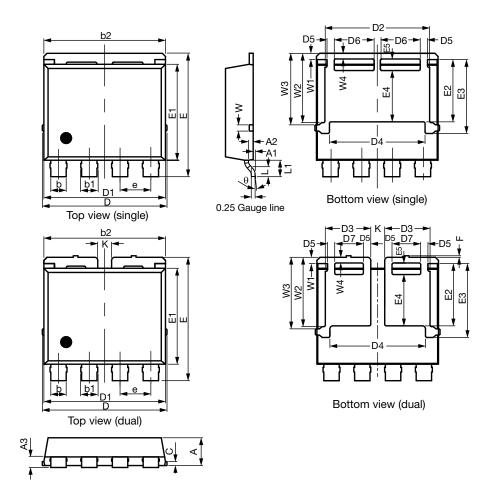


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76718.







DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17

Document Number: 67734

Package Information



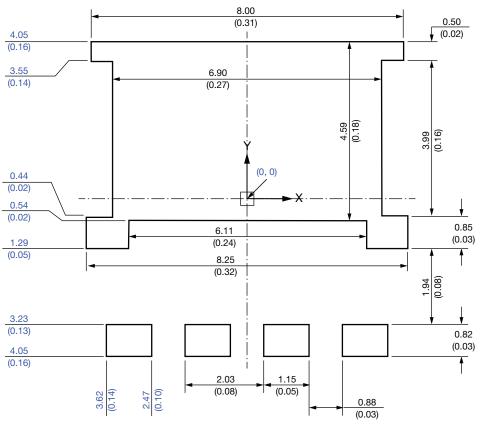


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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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